

**Silicon PNP transistor epitaxial type  
6A020**
**[ Applications ]**

High voltage driver

**[ Feature ]**

High voltage VCEO= VCBO= -300V

**[ Absolute maximum ratings (Ta=25C) ]**

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-300	V
Collector-emitter voltage	VCEO	-300	V
Emitter-base voltage	VEBO	-7	V
Collector current	IC	-100	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

**[ Electrical characteristics (Ta=25C) ]**

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-300	-	-	V	IC= -50uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-300	-	-	V	IC= -10mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-7	-	-	V	IE= -50uA, IC= 0A
Collector-cut off current	ICBO	-	-	-500	nA	VCB= -300V, IE= 0A
DC current gain	hFE	60	-	280	-	VCE= -10V, IC= -10mA
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.5	V	IC= -100mA, IB= -10mA
Transition frequency	fT	-	65	-	MHz	VCE= -10V, IE= 10mA
Collector output capacitance	Cob	-	4.5	-	pF	VCB= -20V, f= 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 hFE - IC  
at VCE= -10V, Ta= 25C

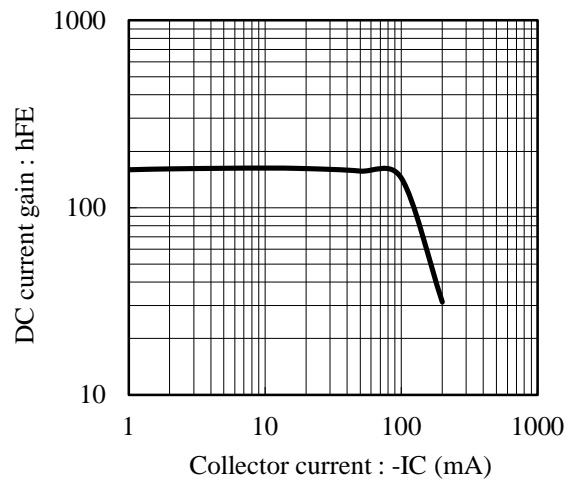


Fig.2 VCE(sat) - IC  
at IC/IB= 10, Ta= 25C

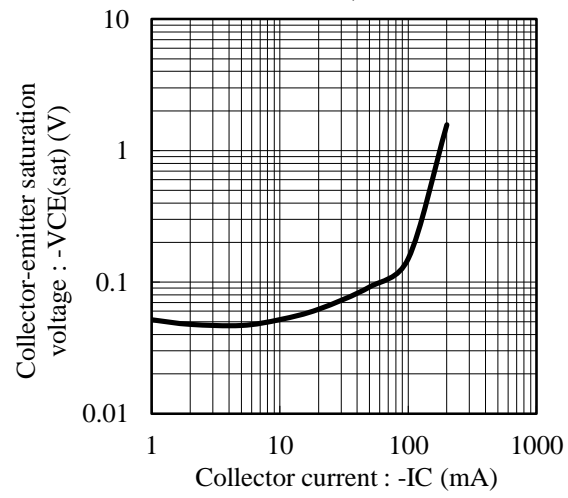


Fig.3 VBE(sat) - IC  
at IC/IB= 10, Ta= 25C

